

FEATURES

- High Speed Switching
- High Blocking Voltage with Low $R_{DS(on)}$
- Easy to Parallel
- Simple to Drive
- RoHS Compliant

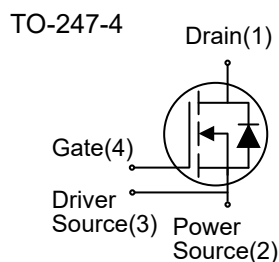
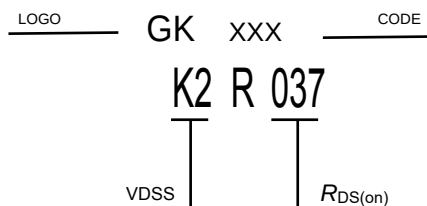
APPLICATION

- Increased Power Density
- Faster Operating Frequency
- Reduction of Heat Sink Requirements
- Higher Efficiency
- Reduced EMI

APPLICATION

- Power Factor Correction Modules
- Switch Mode Power Supplies
- DC-AC Inverters
- High Voltage DC/DC Converters

V_{DS} 1200 V
 I_D 74 A
 $R_{DS(on)}$ 37 m Ω



ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{DS}	Drain-Source Voltage		1200	V
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$	74 52	A
I_{DM}	Peak Drain Current	Pulse width t_p limited by T_{jmax}	150	A
V_{GSmax}	Gate-Source Voltage		-8/+22	V
V_{GSop}	Recommend Gate-Source Voltage		-4/+18	V
P_{tot}	Power Dissipation	$T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$	312 156	W
T_j	Operating Junction Temperature		-40~175	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40~175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D=100\mu\text{A}$, $V_{GS}=0\text{V}$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1200\text{V}$, $V_{GS}=0\text{V}$		1	5	μA
I_{GSS}	Gate-Source Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=18\text{V}$			250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=10\text{mA}$ $T_j=25^{\circ}\text{C}$ $T_j=175^{\circ}\text{C}$	2	2.6 2.0	4	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=18\text{V}$, $I_D=40\text{A}$ $T_j=25^{\circ}\text{C}$ $T_j=175^{\circ}\text{C}$		37 47	50	$\text{m}\Omega$

Dynamic Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{DS}=1000\text{V}$, $f=100\text{kHz}$, $V_{GS}=0\text{V}$		2975		pF
C_{oss}	Output Capacitance			119		pF
C_{rss}	Reverse Transfer Capacitance			12		pF
$R_{G(int)}$	Internal Gate Resistance	$f=1\text{MHz}$		2.1		Ω
Q_g	Total Gate Charge	$V_{DS}=800\text{V}$, $I_D=40\text{A}$, $V_{GS}=-4/18\text{V}$		117		nC
Q_{gs}	Gate to Source Charge			38		nC
Q_{gd}	Gate to Drain Charge			27		nC

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance from Junction to Case		0.48		$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=800\text{V}$, $I_D=40\text{A}$, $V_{GS}=-4\text{V}/18\text{V}$, $R_{G(ext)}=2.5\Omega$, $L=200\mu\text{H}$		18		ns
t_r	Rise Time			21		ns
$t_{d(off)}$	Turn-Off Delay Time			31		ns
t_f	Fall Time			9		ns
E_{on}	Turn-On Energy			485		μJ
E_{off}	Turn-Off Energy			75		μJ

Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{SD}	Diode Forward Voltage	$V_{GS}=-4\text{V}$, $I_{SD}=20\text{A}$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$		5.0 4.4	6.6	V
I_S	Continuous Diode Forward Current	$V_{GS}=-4\text{V}$ $T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$		45 20		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-4\text{V}$, $I_{SD}=40\text{A}$, $V_R=800\text{V}$, $di/dt=3900\text{A}/\mu\text{s}$		19		ns
Q_{rr}	Reverse Recovery Charge			500		nC
I_{rrm}	Peak Reverse Recovery Current			50		A

RATING AND CHARACTERISTIC CURVES

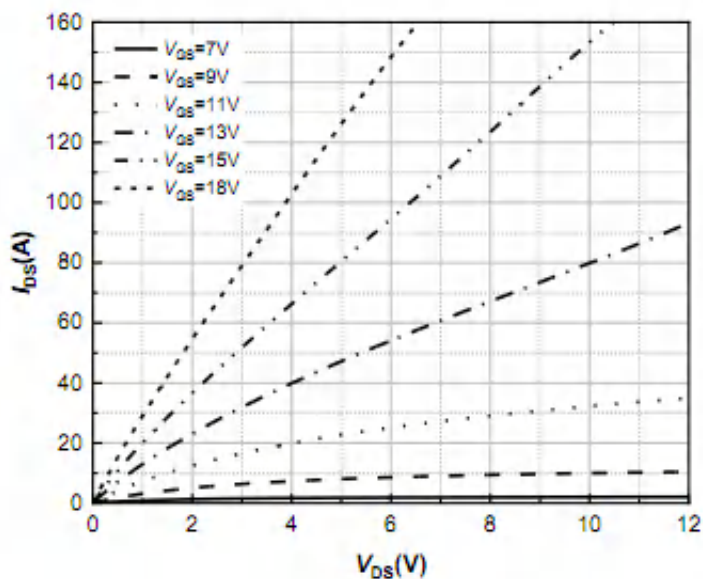


Figure 1. Output Characteristics
 $T_j = -40^\circ\text{C}$

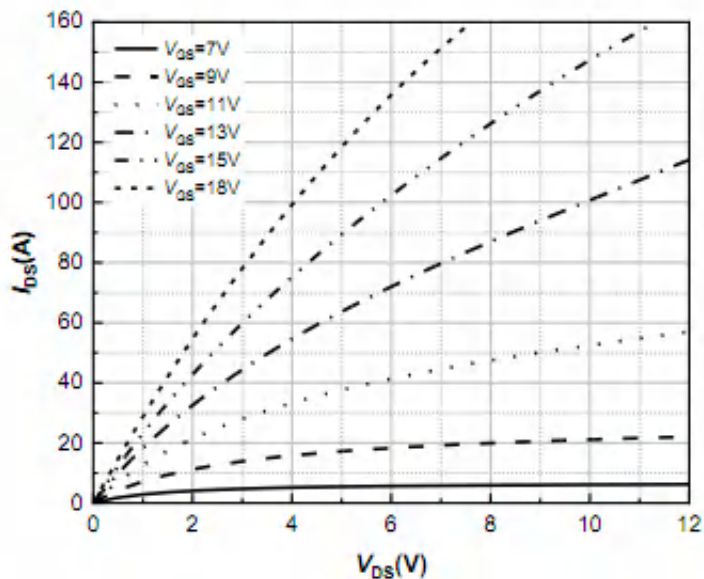


Figure 2. Output Characteristics
 $T_j = 25^\circ\text{C}$

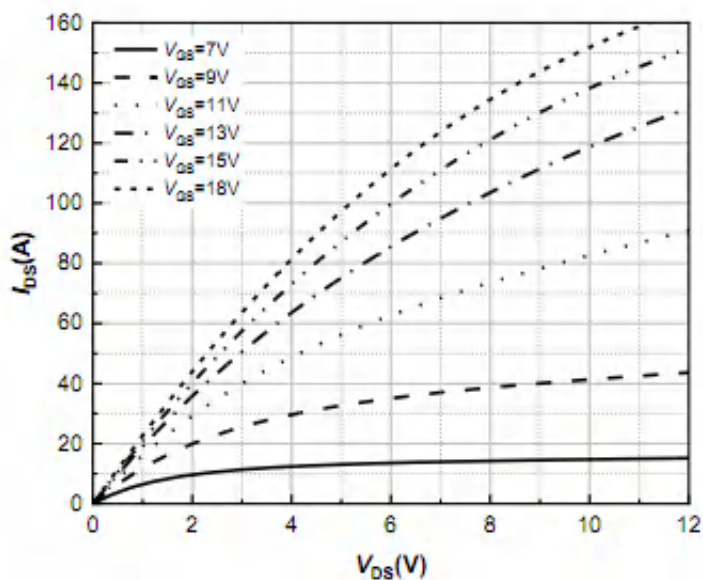


Figure 3. Output Characteristics
 $T_j = 175^\circ\text{C}$

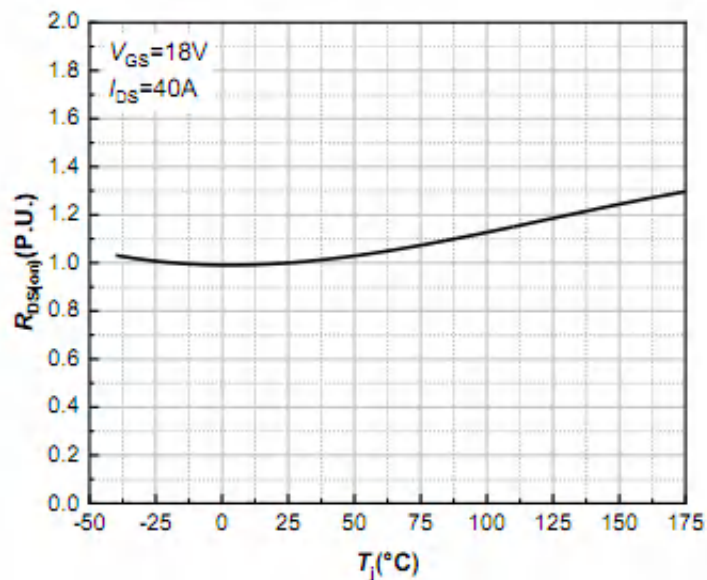


Figure 4. Normalized On-Resistance vs.
Temperature

RATING AND CHARACTERISTIC CURVES

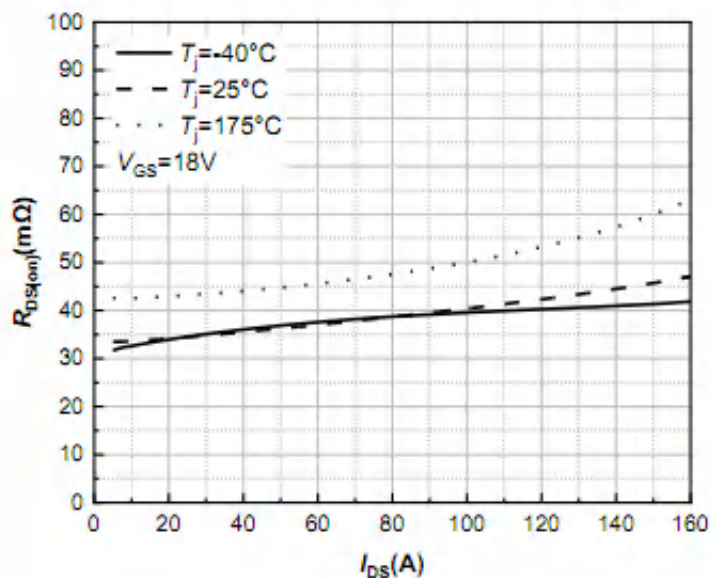


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

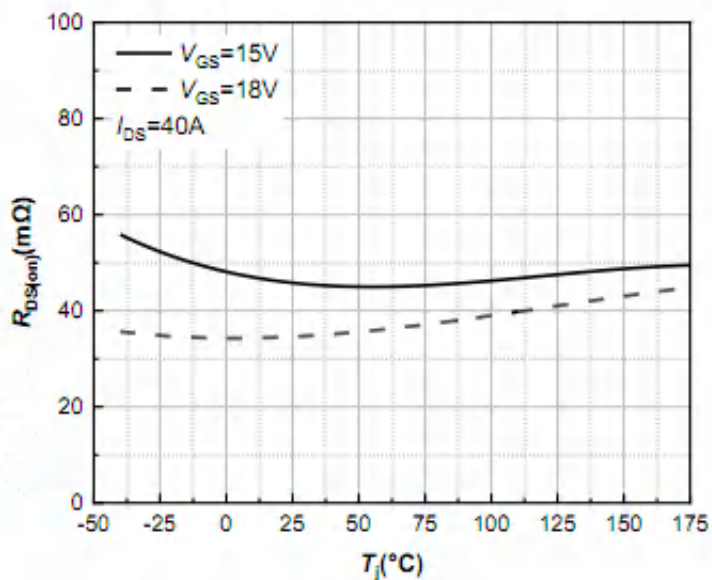


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

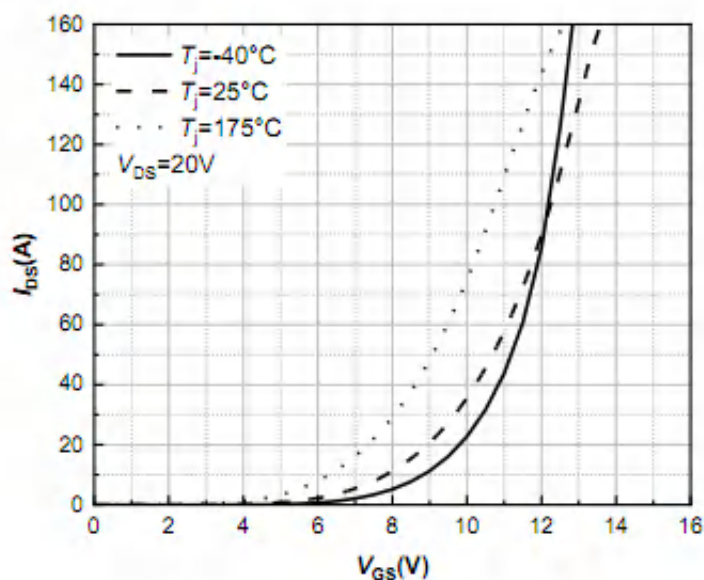


Figure 7. Transfer Characteristic for Various Junction Temperatures

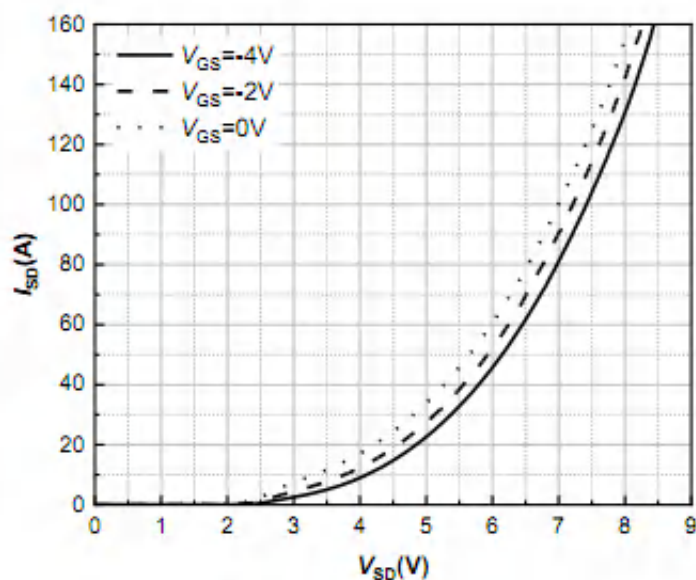


Figure 8. Body Diode Characteristic $T_J = -40^{\circ}\text{C}$

RATING AND CHARACTERISTIC CURVES

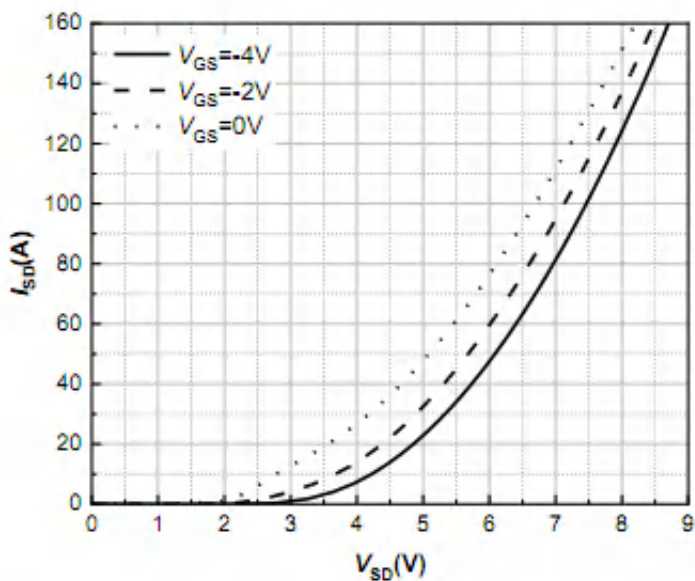


Figure 9. Body Diode Characteristic
 $T_j=25^{\circ}\text{C}$

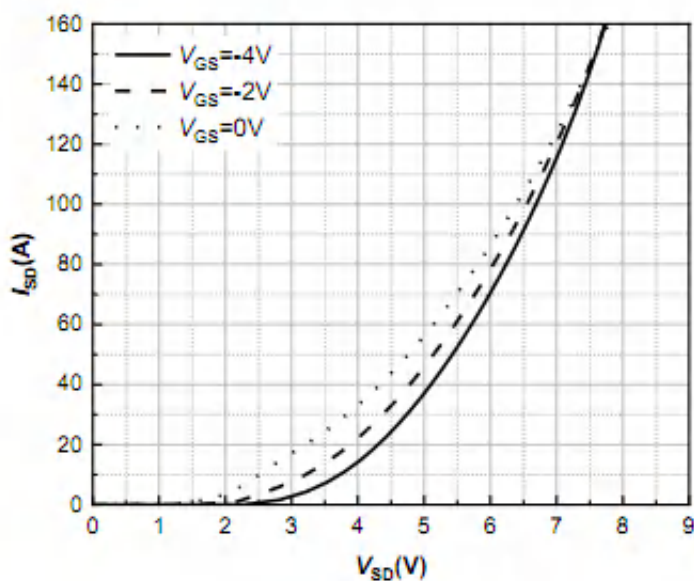


Figure 10. Body Diode Characteristic
 $T_j=175^{\circ}\text{C}$

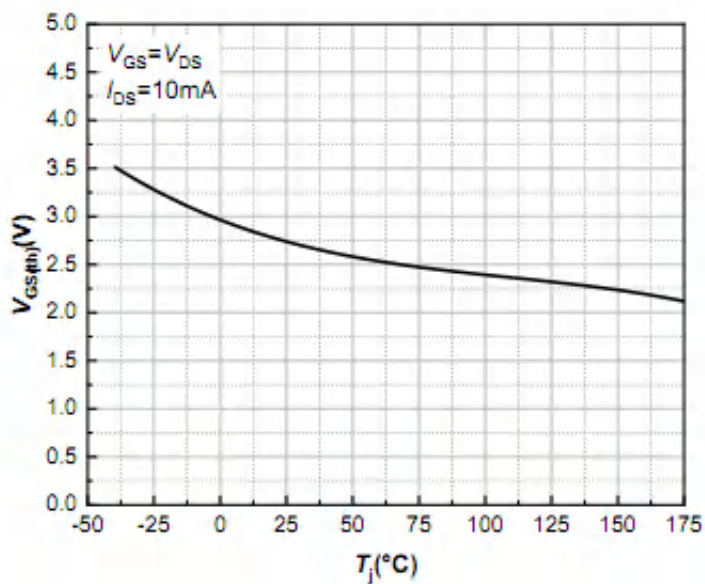


Figure 11. Threshold Voltage vs.
Temperature

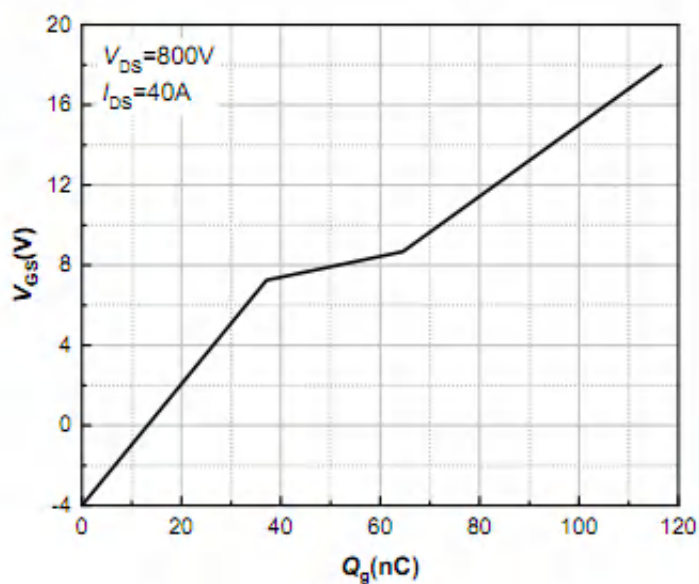


Figure 12. Gate Charge Characteristics

RATING AND CHARACTERISTIC CURVES

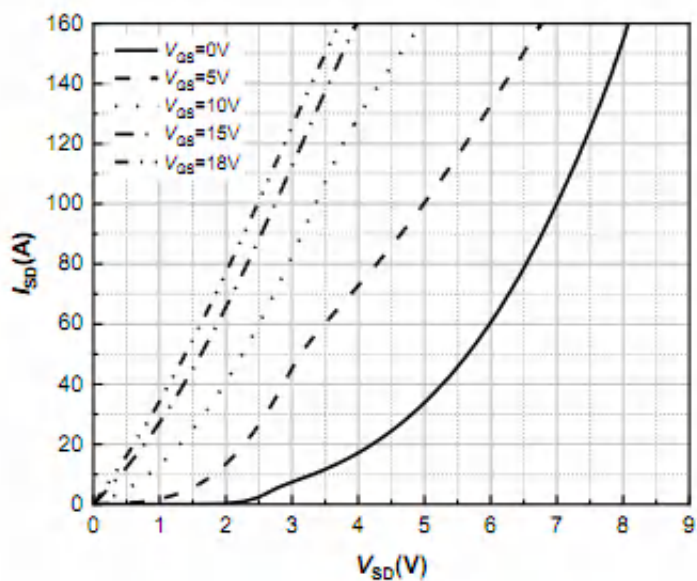


Figure 13. 3rd Quadrant Characteristic
 $T_j = -40^{\circ}\text{C}$

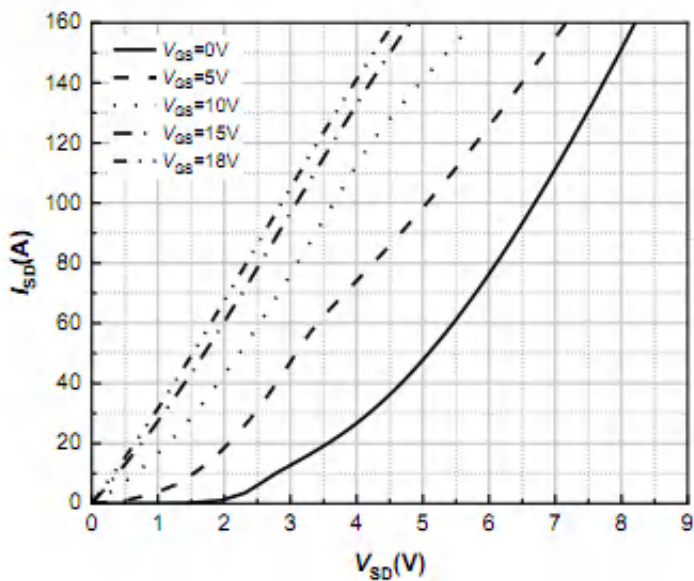


Figure 14. 3rd Quadrant Characteristic
 $T_j = 25^{\circ}\text{C}$

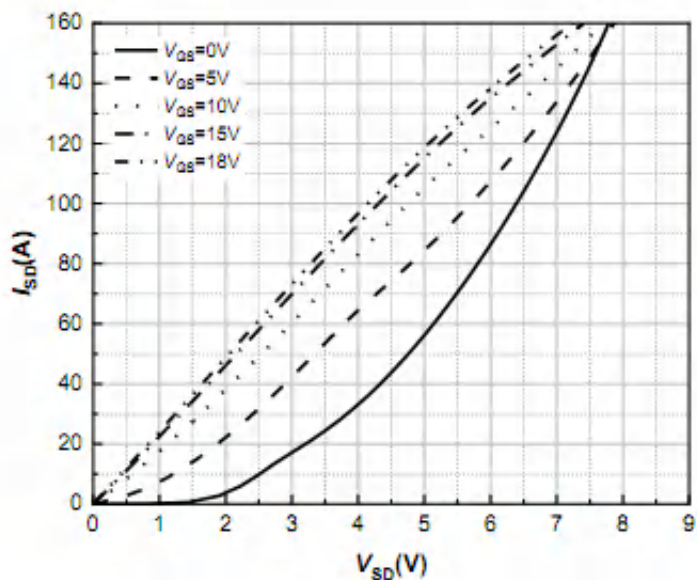


Figure 15. 3rd Quadrant Characteristic
 $T_j = 175^{\circ}\text{C}$

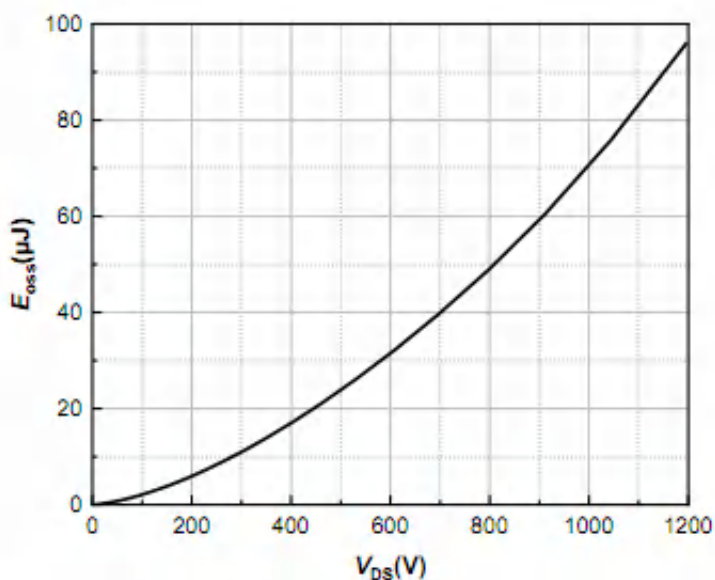


Figure 16. Output Capacitor Stored Energy

RATING AND CHARACTERISTIC CURVES

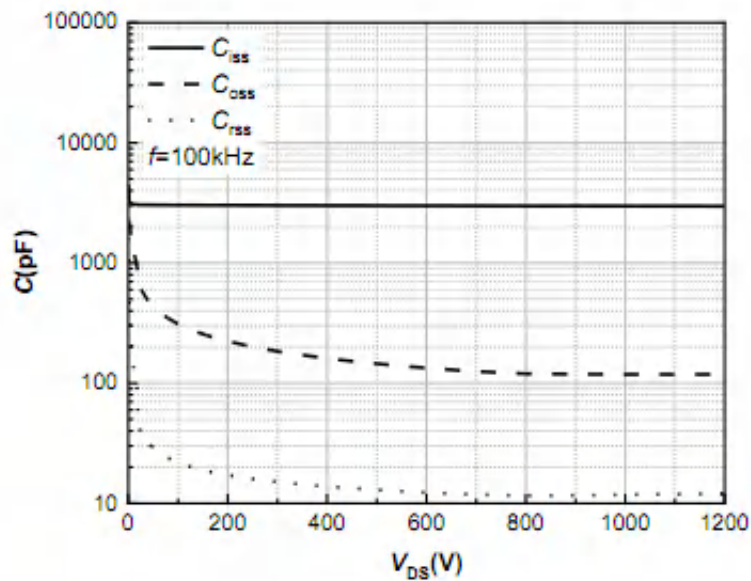


Figure 17. Capacitances vs. Drain-Source

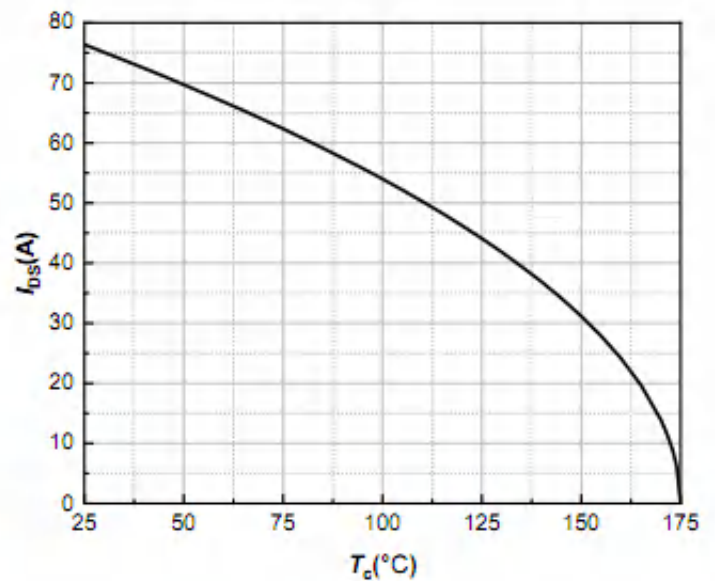


Figure 18. Continuous Drain Current Derating vs. Case Temperature

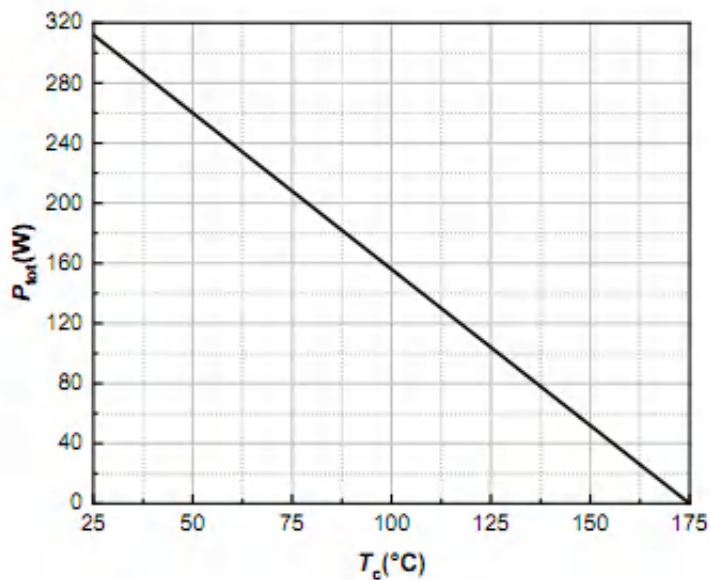


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

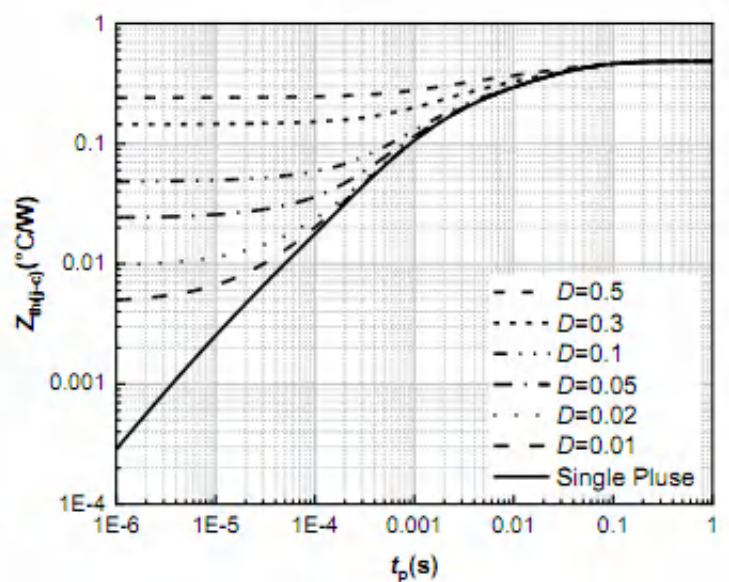


Figure 20. Transient Thermal Impedance

RATING AND CHARACTERISTIC CURVES

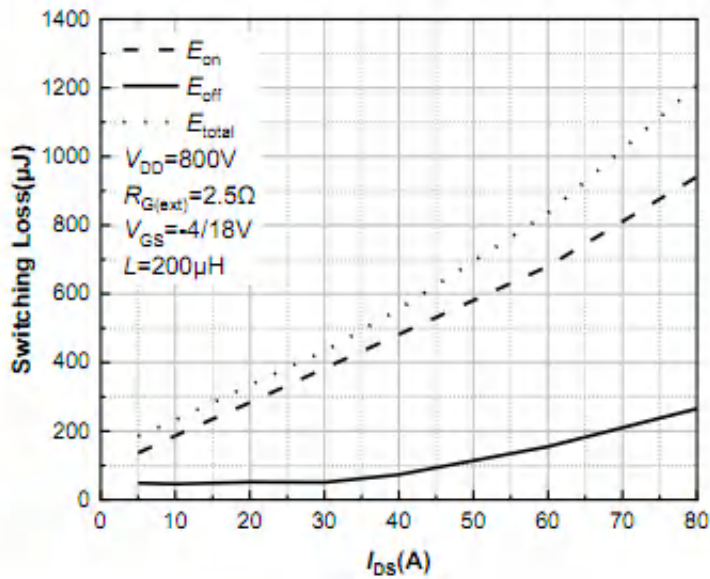


Figure 21. Clamped Inductive Switching Energy vs. Drain Current

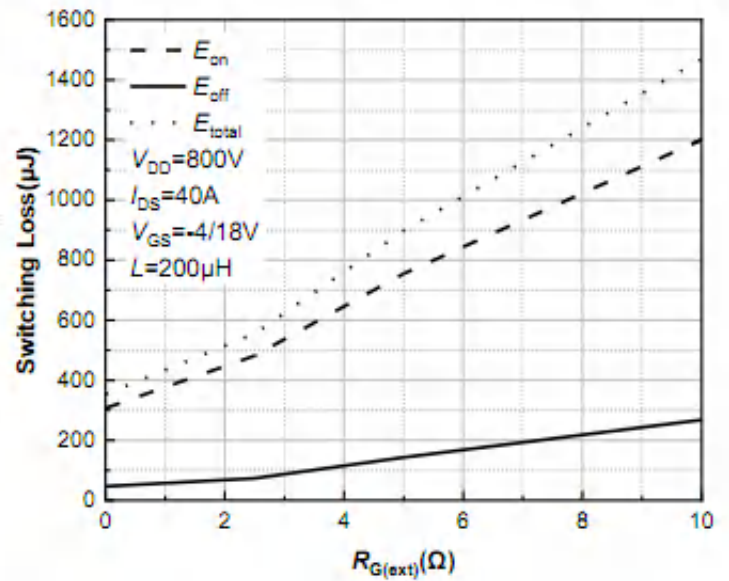


Figure 22. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

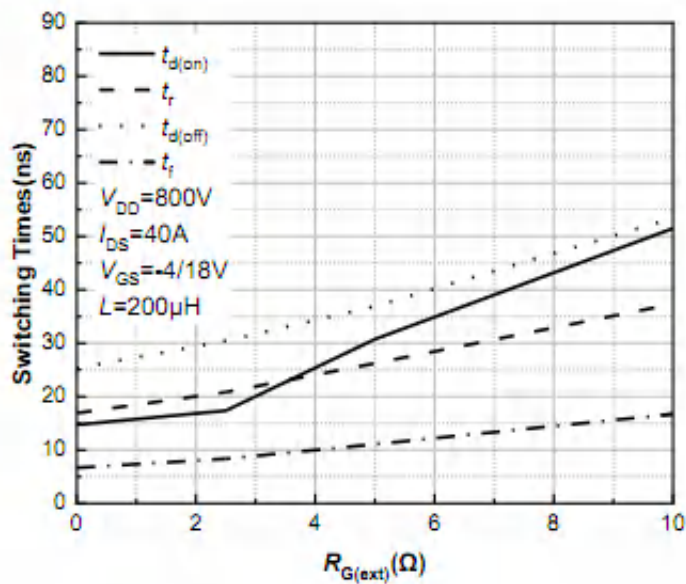


Figure 23. Switching Times vs. $R_{G(ext)}$

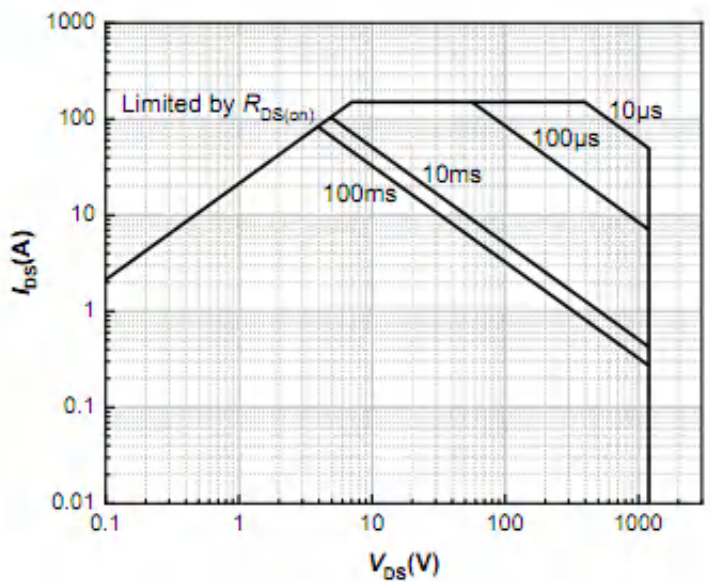
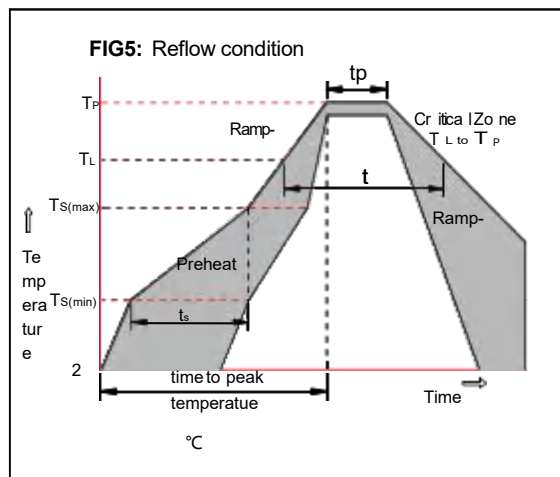


Figure 24. Safe Operating Area

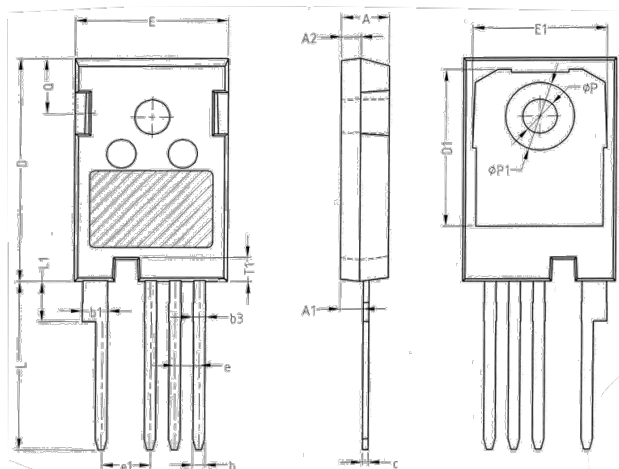
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C



Package Dimensions & Suggested Pad Layout

TO-247-4



SYMBOL	Unit: mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
b	1.06	1.21	1.36
b1	2.33	2.63	2.93
b3	1.07	1.30	1.60
c	0.51	0.61	0.75
D	23.30	23.45	23.60
D1	16.25	16.55	16.85
E	15.74	15.94	16.14
E1	13.72	14.02	14.32
T1	2.35	2.50	2.65
e	2.54 BSC		
e1	5.08 BSC		
Q	5.49	5.79	6.09
L	17.27	17.57	17.87
L1	3.99	4.19	4.39
ΦP	3.40	3.60	3.80
ΦP1	7.19 REF		